

8961726 TEXAS INSTR (OPTO)

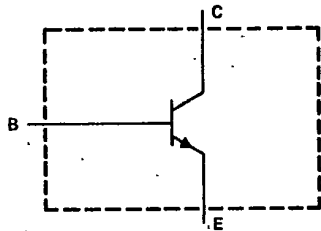
62C 36683 D

**BUY70A, BUY70B, BUY70C**  
**N-P-N SILICON POWER TRANSISTORS**  
*T-33-13*

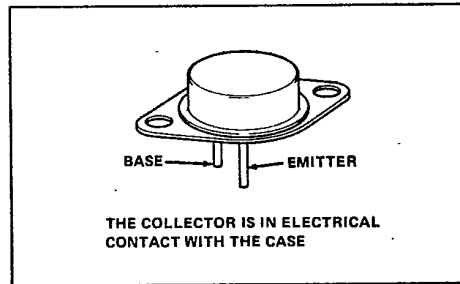
OCTOBER 1982 - REVISED OCTOBER 1984

- 75 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- 15 A Peak Collector Current
- Designed for Switching Mode Power Supplies, Inverters, and CRT Scanning Systems

device schematic



TO-3 PACKAGE



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	BUY70A	BUY70B	BUY70C
Collector-base voltage	1000 V	800 V	500 V
Collector-emitter voltage ( $I_B = 0$ )	400 V	325 V	200 V
Emitter-base voltage	8 V		
Continuous collector current	10 A		
Peak collector current (see Note 1)	15 A		
Continuous base current	3 A		
Continuous device dissipation (see Figure 9) ( $V_{CE} \leq 17$ V)	75 W		
Operating temperature range	- 65°C to 200°C		

NOTE 1: This value applies for  $t_W \leq 500 \mu s$ , duty cycle  $\leq 25\%$ .



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electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	BUY70A			BUY70B			BUY70C			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$V_{(BR)CBO}$	$I_C = 1 \text{ mA}$ , See Note 2 $I_E = 0$	1000			800			500			V
$V_{CE(sus)}$	$I_B = 0$ , $I_C = 50 \text{ mA}$	400			325			200			V
$V_{(BR)EBO}$	$I_B = 10 \text{ mA}$	8			8			8			V
$I_{CEX}$	$V_{CE} = 1000 \text{ V}$ , $V_{BE} = -2 \text{ V}$		1								mA
	$V_{CE} = 800 \text{ V}$ , $V_{BE} = -2 \text{ V}$				1						
	$V_{CE} = 500 \text{ V}$ , $V_{BE} = -2 \text{ V}$							1			
$h_{FE}$	$V_{CE} = 10 \text{ V}$ , See Note 3 $I_{CE} = 1 \text{ A}$	15			15			15			
$V_{BE(sat)}$	$I_B = 0.8 \text{ A}$ , See Note 3 $I_C = 4 \text{ A}$		1.5			1.5			1.5		V
$V_{CE(sat)}$	$I_B = 0.8 \text{ A}$ , See Note 3 $I_C = 4 \text{ A}$		5			5			5		V
$f_T$	$V_{CE} = 10 \text{ V}$ , $I_C = 0.5 \text{ A}$		6			6			6		MHz
$C_{obo}$	$V_{CB} = 20 \text{ V}$ , $I_C = 0$		150			150			150		pF

NOTES: 2. These parameters must be measured using pulse techniques,  $t_w \leq 500 \mu\text{s}$ , duty cycle  $\leq 25\%$ .  
3. These parameters must be measured using pulse techniques,  $t_w \leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$		2.3		°C/W

resistive-load switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_f$	$I_C = 4 \text{ A}$ , $V_{CC} = 40 \text{ V}$ , $I_{B1} = 0.8 \text{ A}$ , $I_{B2} = -0.8 \text{ A}$ , See Figure 1			1	$\mu\text{s}$

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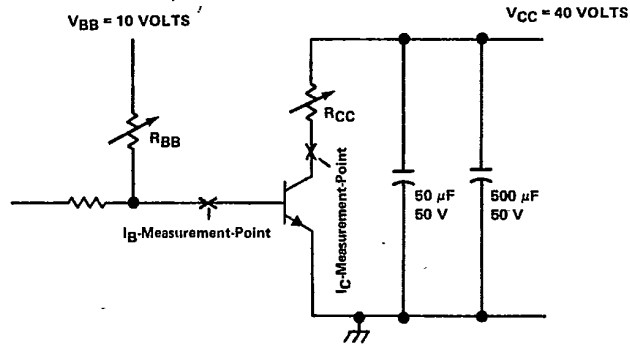
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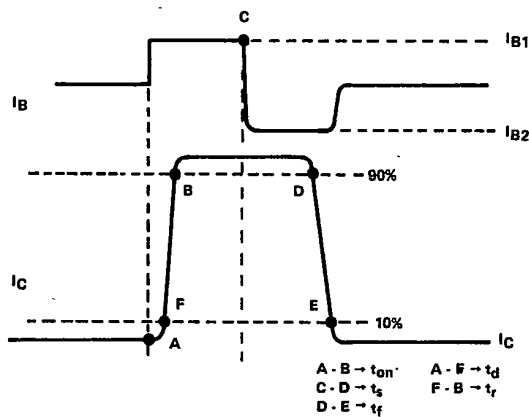
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PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT



VOLTAGE WAVEFORMS

- NOTES: A.  $R_{BB}$  and  $R_{CC}$  adjusted to give  $I_B$  and  $I_C$ .  
 B. Input resistor should correctly terminate pulse generator (normally 50  $\Omega$ ). Input pulse = 25 V,  $t_w = 10 \mu s$ , duty cycle < 2%.  
 C. Oscilloscope rise time less than 20 ns.  
 D. Recommended current probe: Tektronix P6019, P6020, or P6042.  
 E. For typical variation of switching time with collector current, see Figure 4.

FIGURE 1. RESISTIVE-LOAD SWITCHING

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TYPICAL CHARACTERISTICS  
STATIC FORWARD CURRENT TRANSFER RATIO  
VS  
COLLECTOR CURRENT

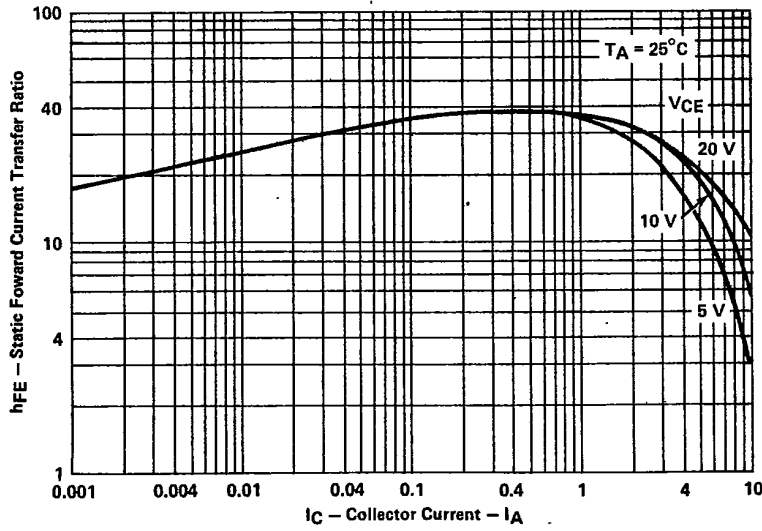


FIGURE 2



BD, BDW, BDX, BU, BUX, BUY Devices

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TYPICAL CHARACTERISTICS

COLLECTOR-EMITTER  
SATURATION VOLTAGE  
vs  
COLLECTOR CURRENT

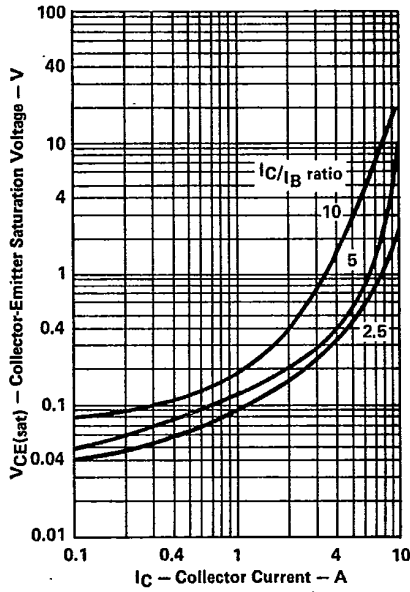


FIGURE 3

SWITCHING TIMES  
vs  
COLLECTOR CURRENT

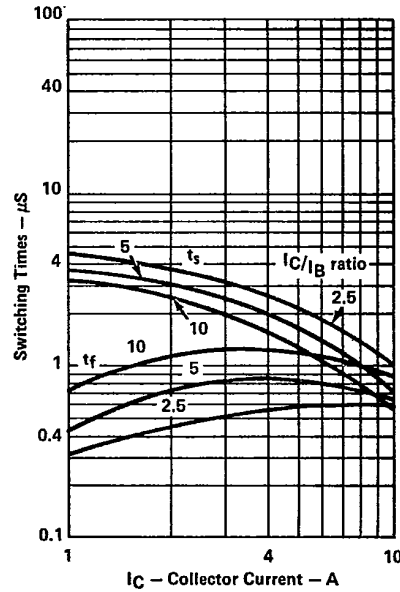


FIGURE 4



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TYPICAL CHARACTERISTICS  
COLLECTOR-BASE LEAKAGE CURRENT  
vs  
TEMPERATURE

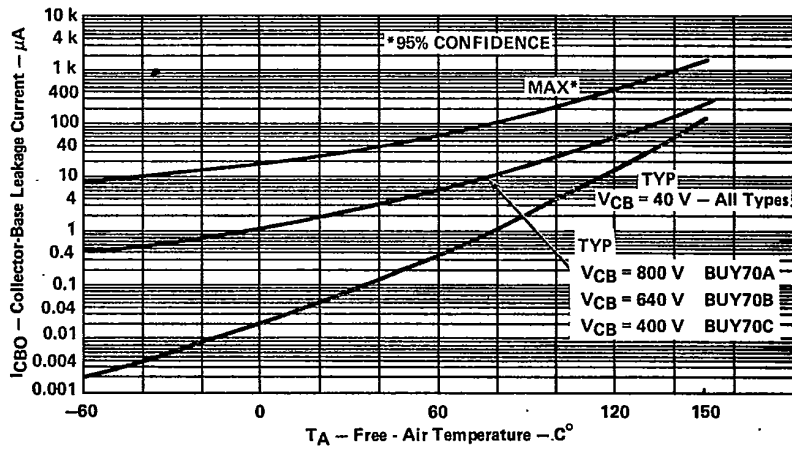


FIGURE 5

BASE-EMITTER SATURATION VOLTAGE  
vs  
COLLECTOR CURRENT

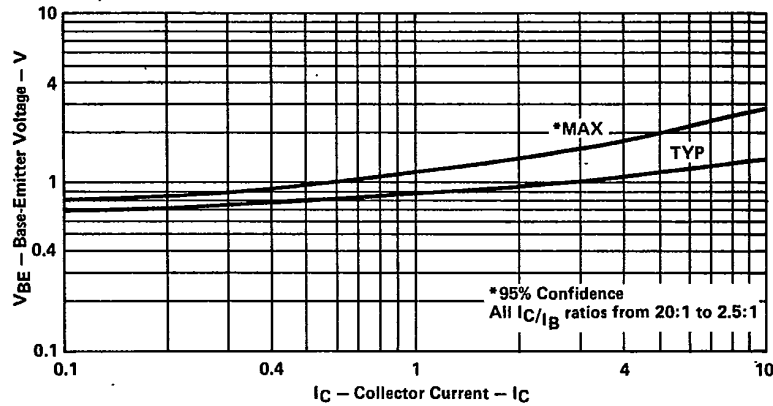


FIGURE 6

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TYPICAL CHARACTERISTICS

TRANSITION FREQUENCY  
vs  
COLLECTOR CURRENT

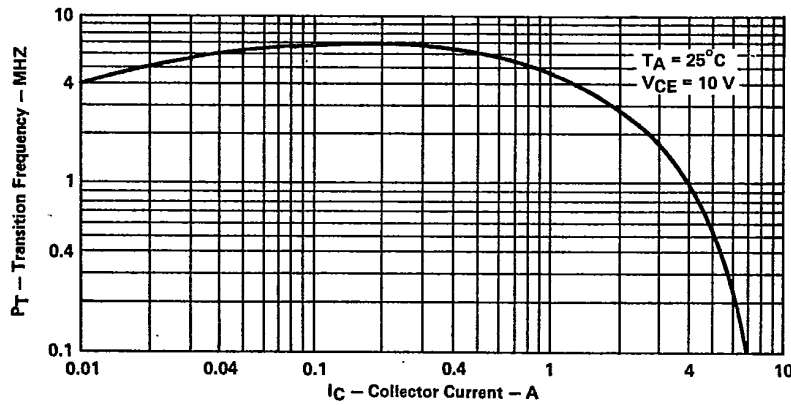


FIGURE 7

MAXIMUM SAFE OPERATING AREA  
FORWARD-BIAS SAFE OPERATING AREA

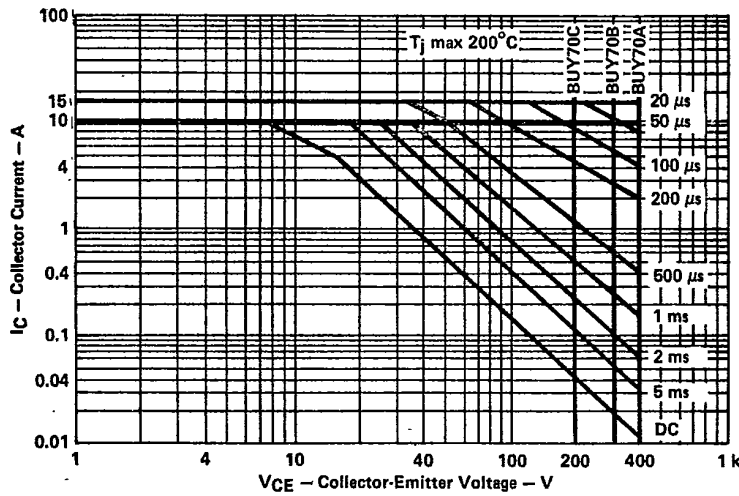


FIGURE 8



BD, BDW, BDX, BU, BUX, BUY, BUY Devices

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THERMAL INFORMATION  
DISSIPATION DERATING CURVE

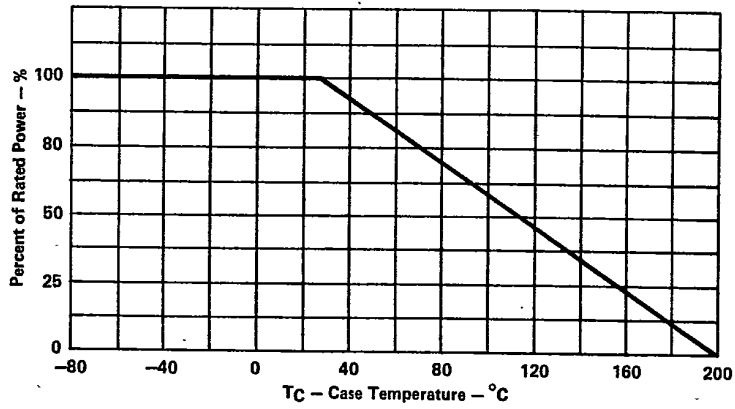


FIGURE 9



BD, BDW, BDX, BU, BUX, BUY Devices

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Datasheets for electronic components.

# Texas Instruments

<http://www.ti.com>

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BUY70A - <http://www.ti.com/product/buy70a?HQS=TI-null-null-dscatalog-df-pf-null-ww>



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